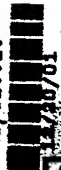


3578 U.S. PTO
10/033328



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U.S. UTILITY Patent Application

PATENT NUMBER and
ISSUE DATE

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10023328	12/20/2001	438	2.0	1765	Lin

****APPLICANTS:** Qi Wen-Jie; Pellerin John; En William; Michael Mark; Chan Darin;

****CONTINUING DATA VERIFIED:**

**** FOREIGN APPLICATIONS VERIFIED:**

PG-PUB	DO NOT PUBLISH <input checked="" type="checkbox"/>	RESCIND <input type="checkbox"/>
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no 35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no Verified and Acknowledged Examiners's initials		ATTORNEY DOCKET NO 50432-485
TITLE : Nitride offset spacer to minimize silicon recess by using poly reoxidation layer as etch stop layer		

U S DEPT. OF COMM./PAT & TM-PTO-436L (Rev. 12-94)

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G.
ISSUE FEE		DRAWING	
Amount Due	Date Paid	Sheets Drwg.	Figs.Drwg. Print Fig.
		Application Examiner	
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE WARNING: The information disclosed herein may be restricted. Unauthorized disclosure may be prohibited by the United States Code Title 35, Sections 122, 181 and 368, Possession outside the U.S. Patent & Trademark Office is restricted to authorized employees and contractors only.	

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